TOSHIBA Photocoupler Photorelay

TLP4597G

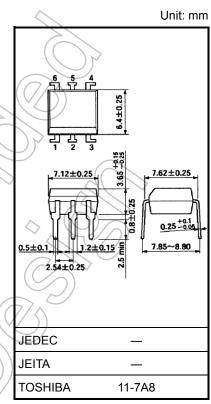
PBX Telecommunication Modem · FAX Cards, Modems In PC Measurement Instrumentation

The TOSHIBA TLP4597G consists of an infrared emitting diode optically coupled to a photo-MOSFET in a six lead plastic DIP package (DIP6).

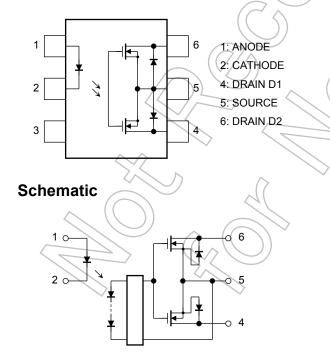
The TLP4597G is a bi-directional switch which can replace mechanical relays in many applications.

- 6 pin DIP (DIP6)
- 1-form-B
- Peak off-state voltage: 350 V (min)
- Trigger LED current: 3 mA (max)
- On-state current: 150 mA (max)
- On-state resistance: 25Ω (max)
- Isolation voltage: 2500 Vrms (min)
- UL-recognized: UL 1577, File No. E67349

Pin Configuration (top view)



Weight: 0.4 g (typ.)



Absolute Maximum Ratings (Ta = 25°C)

$\begin{array}{ c c c c c c } \hline Diode power dissipation & P_D & 50 & mW \\ \hline Diode power dissipation derating (Ta \geq 25^{\circ}C) & & & & & & & & & \\ \hline Junction temperature & T_j & 125 & ^{\circ}C & & & & & & \\ \hline Junction temperature & T_j & 125 & ^{\circ}C & & & & & & \\ \hline Off-state output terminal voltage & VOFF & 350 & V & & & & \\ \hline On-state current & A connection & & & & & & & \\ \hline On-state current & A connection & & & & & & & & \\ \hline On-state current & A connection & & & & & & & & \\ \hline On-state current & A connection & & & & & & & & & \\ \hline On-state current & A connection & & & & & & & & & & & \\ \hline On-state current & A connection & & & & & & & & & & & & & \\ \hline On-state current & A connection & & & & & & & & & & & & & & & & & & &$				-		
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$\begin{array}{ c c c c c c } \hline C \ connection \\ \hline C \ connect$			A connection		150	
$\begin{array}{ c c c c c c c }\hline On-state current derating (Ta \geq 25^{\circ}C) & \hline A \ connection \\ \hline B \ connection \\ \hline C \ conection \\ \hline C \ $	0	n-state current	B connection	ION	150	mA
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$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	0	n-state current	A connection		-1.5	770
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	de	erating	B connection	∆l _{ON} /°C	-1.5	mA/°C
$\begin{array}{ c c c c c c c c c c c c c c c c c c c$	() ctor	a ≥ 25°C)	C connection		-3.0	
$\begin{array}{ c c c c c c c c c c c c c c c c c c c$	Detector		A connection		506	→ mW
$\begin{tabular}{ c c c c c c } \hline C & connection & 567 & & & & & & & & & & & & & & & & & & &$	- 10		B connection	Po	283	
		•	C connection	(567	
$\begin{array}{ c c c c c c c c c c c c c c c c c c c$	0	utput power	A connection		-5.06	
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Depending temperature range Topr -40 to 85 °C porage temperature range Tstg -55 to 125 °C ad soldering temperature (10 s) Tsol 260 °C polation voltage D)/a 2500 V/max	((Ta ≥ 25°C)	C connection		-5.67	$\langle \rangle$
orage temperature range Tstg -55 to 125 °C ad soldering temperature (10 s) Tsol 260 °C olation voltage D)/a 2500 V/max	Ju	unction temperate	ure	(t _j	125	ିଦ
orage temperature range Tstg -55 to 125 °C ad soldering temperature (10 s) Tsol 260 °C olation voltage D)/a 2500 V/max	Operati	ing temperature r	ange	Topr	-40 to 85	°C
plation voltage	Storage	e temperature rar	nge		-55 to 125	°C
Dilation voltage BVs 2500 Vrms C, 60 s, R.H. ≤ 60 %) (Note 1) BVs 2500 Vrms	Lead so	oldering temperat	ture (10 s)	Tsol	260	°C
	Isolatio (AC, 60	n voltage) s, R.H. ≤ 60 %)	(Note 1)	BVs	2500	Vrms

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Device considered a two-terminal device: LED side pins shorted together, and DETECTOR side pins shorted together.

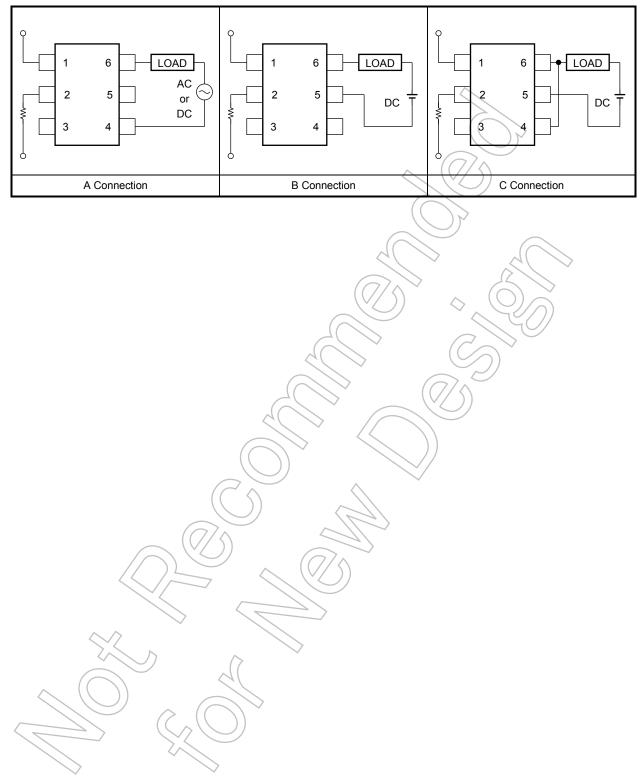
Recommended Operating Conditions

Characteristics	Symbol	Min	Тур.	Max	Unit
Supply voltage	V _{DD}	—	_	280	V
Forward current	lF	5	_	25	mA
On-state current	ION	—	—	150	mA
Operating temperature	T _{opr}	-20		65	°C

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.

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Circuit Connections



Individual Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
	Forward voltage	VF	I _F = 10 mA	1.0	1.15	1.3	V
LED	Reverse current	I _R	$V_R = 5 V$	_	_	10	μA
	Capacitance	CT	V = 0 V, f = 1 MHz	/-	30	_	pF
Detector	Off-state current	IOFF	V _{OFF} = 350 V, I _F = 5 mA	\langle		1	μA
Dete	Capacitance	COFF	V = 0 V, f = 1 MHz, I _F = 5 mA		65		pF

Coupled Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Trigger LED current		IFC	IOFF = 10 μA	—	$\sqrt{1}$	3	mA
Return LED current		IFT	ION = 150 mA	0.1	X		mA
	A connection	Ron	ION = 150 mA	-(C)15	25	
On-state resistance	B connection		Ion = 150 mA	8			Ω
	C connection		ION = 300 mA		4	_	

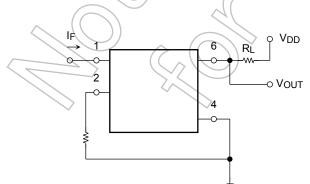
Isolation Characteristics (Ta = 25°C)

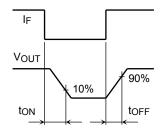
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Capacitance input to output	Cs	Vs = 0 V, f = 1 MHz	—	0.8	_	pF
Isolation resistance	Rs	V _S = 500 V, R.H. ≤ 60 %	5 × 10 ¹⁰	10 ¹⁴		Ω
Isolation voltage	BVs	AC, 60 s	2500			Vrms

Switching Characteristics ($Ta = 25^{\circ}C$)

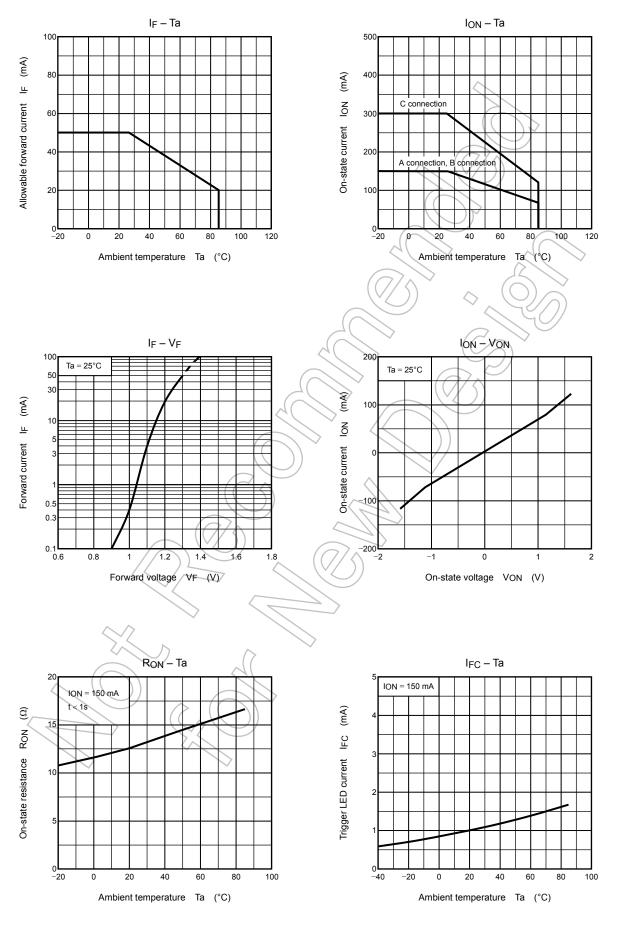
Characteristics	Symbol Test Condition		Min	Тур.	Max	Unit
Turn-on time	ton $R_{\rm L} = 200 \Omega$	(Note 2)	_	_	1	ms
Turn-off time	t _{OFF} V _{DD} = 20 V, I _F = 5 mA		_	_	3	ms

Note 2: Switching time test circuit

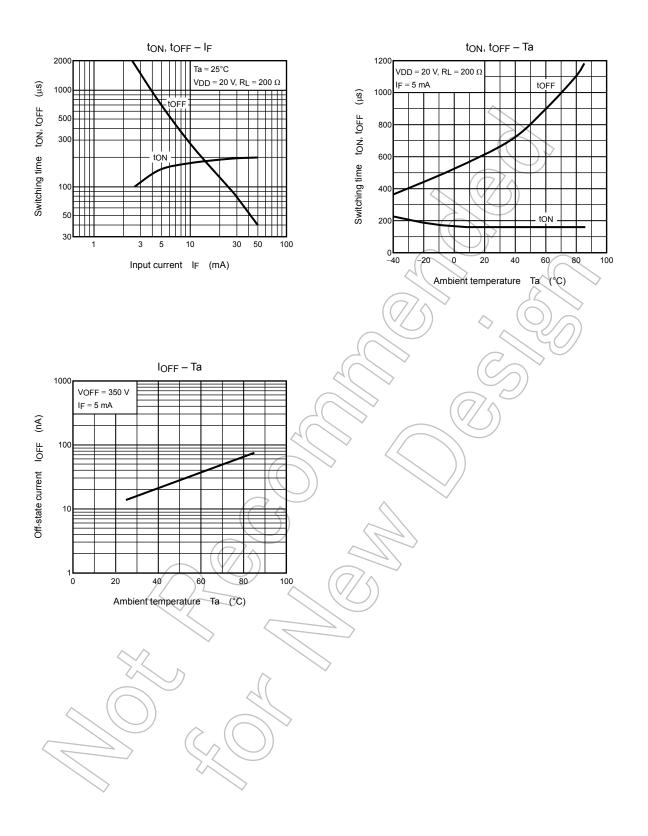




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NOTE: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted. 5



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